

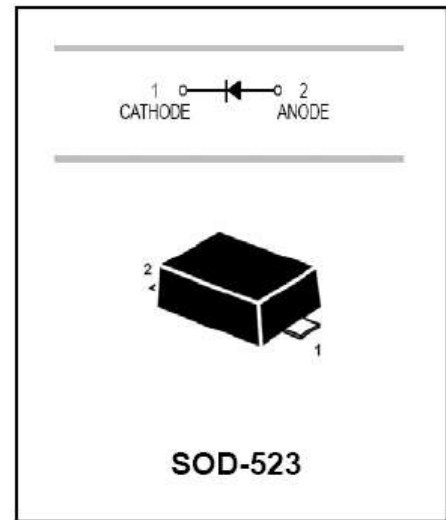
## High speed Switching Diode

### FEATURES

- Extremely small surface mounting type.
- Small package.
- High speed and high reliability

### APPLICATIONS

- High speed switching.



MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	90	V
DC Reverse voltage	$V_R$	80	V
Continuous forward current	$I_F$	225	mA
Surge current	$I_{FSM}$	0.5	A
Total power dissipation	$P_{tot}$	150	mW
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55-125	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$			1.2	V	$I_F=100mA$
Reverse current	$I_R$			20	$\mu A$	$V_R=80V$
Diode capacitance	$C_d$		0.72	3.0	pF	$V_R=0.5V, f=1MHz$
Reverse recovery time	$t_{rr}$			4	ns	$V_R=6V, I_F=10mA, R_L=100\Omega$

TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

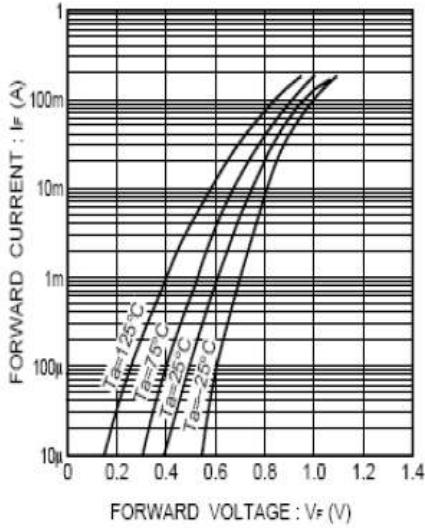


Fig.1 Forward characteristics

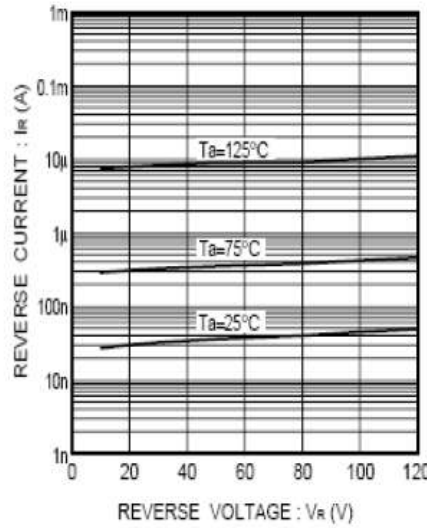


Fig.2 Reverse characteristics

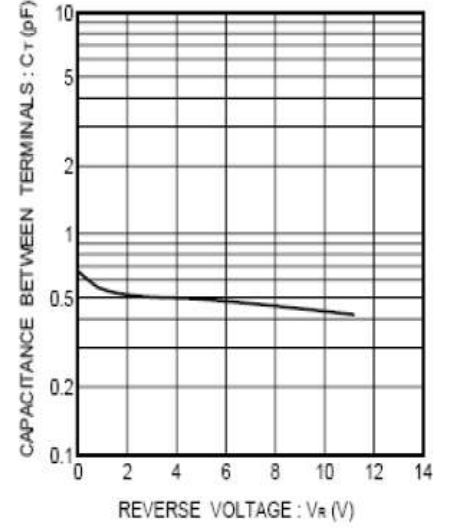


Fig.3 Capacitance between terminals

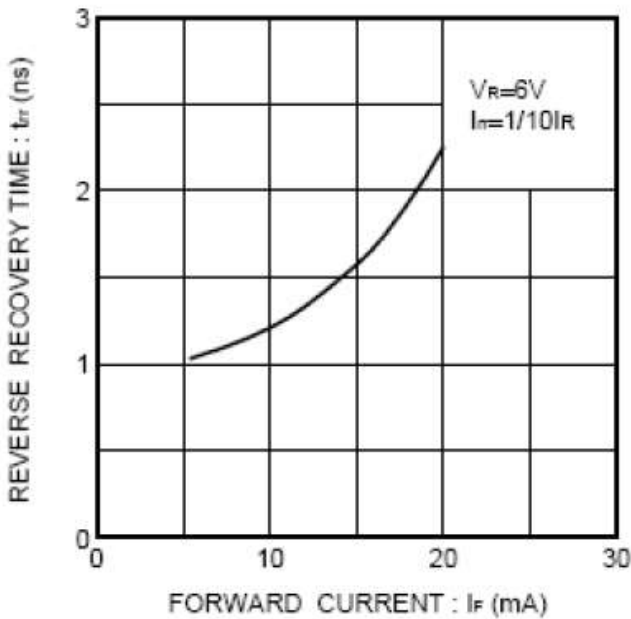


Fig.4 Reverse recovery time characteristics

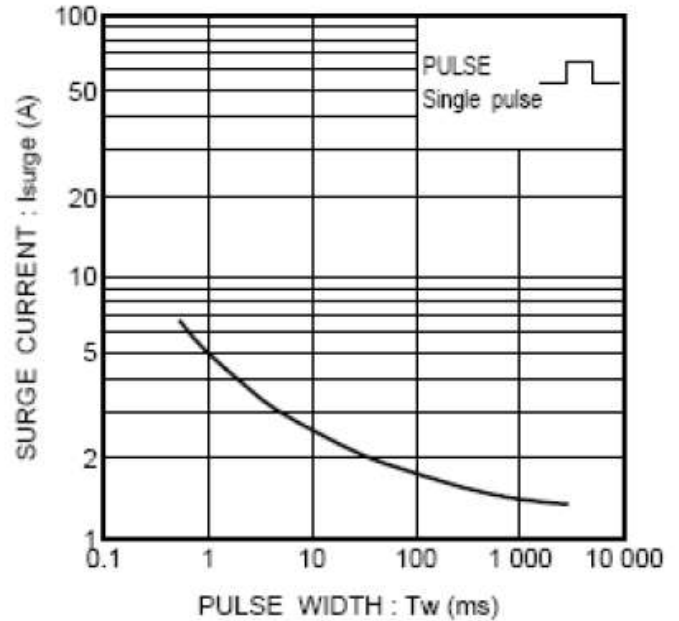


Fig.5 Surge current characteristics